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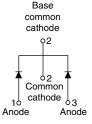
Hyperfast Rectifier, 2 x 10 A FRED Pt®





TO-220AB

TO-220 FULL-PAK





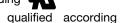
VS-20CTH03PbF VS-20CTH03-N3

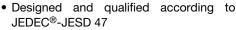
VS-20CTH03FPPbF VS-20CTH03FP-N3

PRODUCT SUMMARY					
Package TO-220AB, TO-220FR					
I _{F(AV)}	2 x 10 A				
V_{R}	300 V				
V _F at I _F	0.85 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending





· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





RoHS **HALOGEN FREE**

DESCRIPTION / APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage		V_{RRM}		300	V				
Average rectified forward current	per diode	I _{F(AV)}	T _C = 160 °C	10					
	(FULL-PAK) per diode		T _C = 135 °C						
	per device			20	А				
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	120					
Operating junction and storage temperatures		T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. TYP. I				
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	300	-	-		
Forward voltage		I _F = 10 A	-	1.05	1.25	V	
	V _F	I _F = 10 A, T _J = 125 °C	-	0.85	0.95		
Reverse leakage current I _R	1	V _R = V _R rated	-	-	20		
	I IR	$T_J = 125 ^{\circ}C$, $V_R = V_R$ rated	-	6	200	μA	
Junction capacitance	C _T	V _R = 300 V	-	30	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1 A, dI_F/dt = 50 A$	Vμs, V _R = 30 V	-	-	35		
		$I_F = 1 A, dI_F/dt = 100$	$A/\mu s$, $V_R = 30 V$	-	-	30	ns ns	
	t _{rr}	T _J = 25 °C		-	31	-		
		T _J = 125 °C		-	42	-		
Dook recovery ourrent		T _J = 25 °C	$I_F = 10 \text{ A}$	-	2.4	-	Α	
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	5.6	-	_ ^	
Reverse recovery charge		T _J = 25 °C		-	36	-	200	
	Q _{rr}	T _J = 125 °C		-	120	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDTIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction an temperature range	d storage	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance,	per diode		-	-	1.5	°C/W			
junction to case	(FULL-PAK) per diode	R_{thJC}	and greased	-	-	3.9	C/VV		
Marking device			Case style TO-220AB	20CTH03					
		Case style TO-220 FULL-PAK		20CTH03FP					

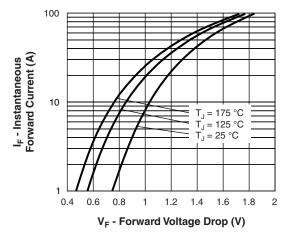


Fig. 1 - Typical Forward Voltage Drop Characteristics

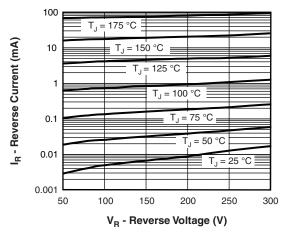


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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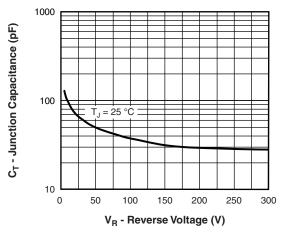


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

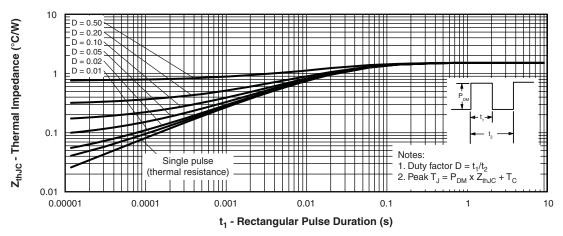


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

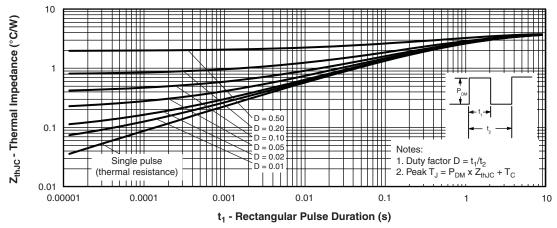


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

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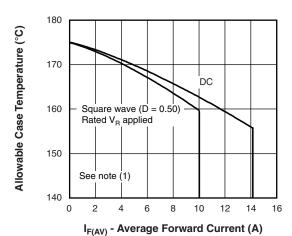


Fig. 6 - Maximum Allowable Case Temperature vs.

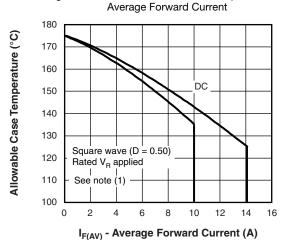


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

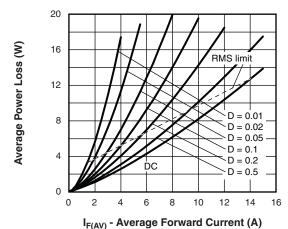


Fig. 8 - Forward Power Loss Characteristics

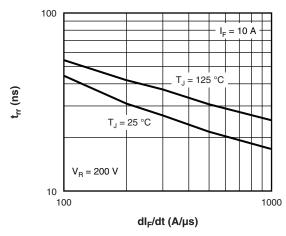


Fig. 9 - Typical Reverse Recovery Time vs. dl_F/dt

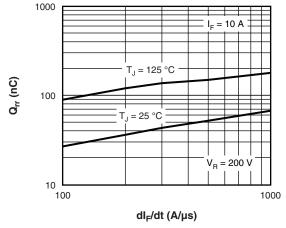


Fig. 10 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)} \ \, \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R (1 - D); I_R \text{ at } V_{R1} = \text{Rated } V_R$

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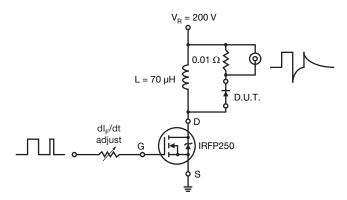
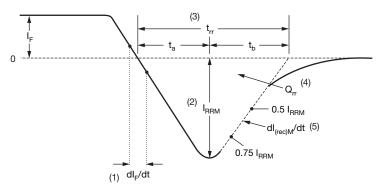


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

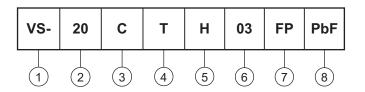
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (20 = 20 A)

3 - C = common cathode

T = TO-220, D²PAK

5 - H = hyperfast recovery

Voltage rating (03 = 300 V)

7 - • None = TO-220AB

• FP = TO-220 FULL-PAK

8 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

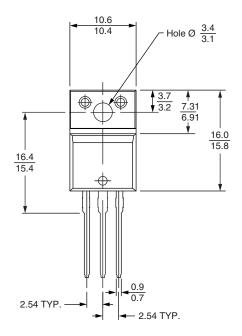
-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

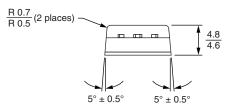
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-20CTH03PbF	50	1000	Antistatic plastic tube				
VS-20CTH03-N3	50	1000	Antistatic plastic tube				
VS-20CTH03FPPbF	50	1000	Antistatic plastic tube				
VS-20CTH03FP-N3	50	1000	Antistatic plastic tube				

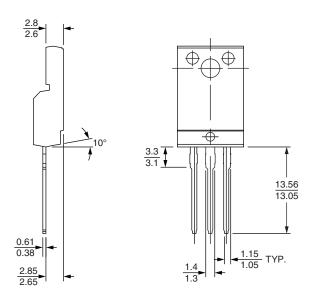
LINKS TO RELATED DOCUMENTS							
Dimensions	TO-220AB	www.vishay.com/doc?95222					
Differsions	TO-220FP	www.vishay.com/doc?95072					
	TO-220ABPbF	www.vishay.com/doc?95225					
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028					
Fart marking information	TO-220FPPbF	www.vishay.com/doc?95069					
	TO-220FP-N3	www.vishay.com/doc?95456					

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DIMENSIONS in millimeters







Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

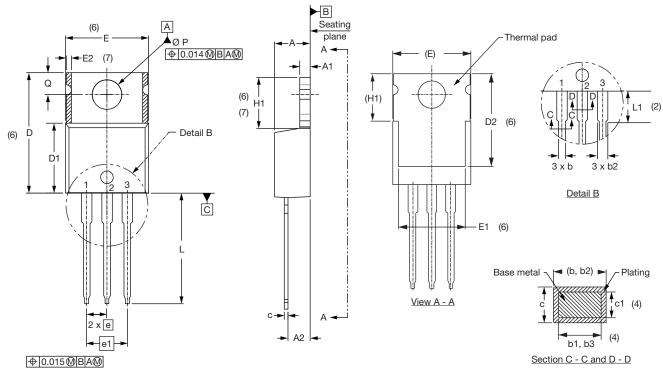
Conforms to JEDEC outline TO-220 FULL-PAK



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TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

Lead assignments

<u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIMETERS		INC	INCHES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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